Minjoo L Lee

List of Publications by Year
in descending order

189	5,769	81839	88593
papers	citations	39 h-index	70 g-index

189	189	189	6583
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Selective Area Heteroepitaxy of p-i-n Junction GaP Nanopillar Arrays on Si (111) by MOCVD. IEEE Journal of Quantum Electronics, 2022, 58, 1-6.	1.0	3
2	Improving the performance of GaInP solar cells through rapid thermal annealing and delta doping. Solar Energy Materials and Solar Cells, 2022, 241, 111725.	3.0	4
3	Delta-Doping for Enhanced III-V Tunnel Junction Performance. IEEE Journal of Photovoltaics, 2022, 12, 976-981.	1.5	1
4	2.0â€“2.2ÂeV AlGaInP solar cells grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 2021, 219, 110774.	3.0	11
5	Graded buffer Bragg reflectors with high reflectivity and transparency for metamorphic optoelectronics. Journal of Applied Physics, 2021, 129, 173102.	1.1	9
6	Comparison of 1.9 eV InGaP front- and rear-junction solar cells grown on Si. , 2021, , .		0
7	Reducing the dependence of threading dislocation density on doping for GaAsP/GaP on Si. , 2021, , .		0
8	Metamorphic 1.7 eV InGaP front- and rear-junction solar cells with high open- circuit voltage. , 2021, , .		1
9	Low-threshold InP quantum dot and InGaP quantum well visible lasers on silicon (001). Optica, 2021, 8, 1495.	4.8	10
10	Challenges of relaxed n-type GaP on Si and strategies to enable low threading dislocation density. Journal of Applied Physics, 2021, 130, 243104.	1.1	5
11	Current-Matched IIIâ€“V/Si Epitaxial Tandem Solar Cells with 25.0% Efficiency. Cell Reports Physical Science, 2020, 1, 100208.	2.8	36
12	InP quantum dots for dislocation-tolerant, visible light emitters on Si. Applied Physics Letters, 2020, 117, .	1.5	8
13	Relaxed GaP on Si with low threading dislocation density. Applied Physics Letters, 2020, 116, 042102.	1.5	14
14	Epitaxial GaAsP/Si Solar Cells with High Quantum Efficiency. , 2020, , .		2
15	Enhanced room temperature infrared LEDs using monolithically integrated plasmonic materials. Optica, 2020, 7, 1355.	4.8	9
16	Importance of Long-lifetime n-GaInP for High-efficiency GaInP Solar Cells Grown by MBE. , 2020, , .		1
17	Effects of Graded Buffer Design and Active Region Structure on GaAsP Single-Junction Solar Cells Grown on GaP/Si Templates. , 2020, , .		1
18	20%-efficient epitaxial GaAsP/Si tandem solar cells. Solar Energy Materials and Solar Cells, 2019, 202, 110144.	3.0	33

#	Article	IF	Citations
19	Selective area epitaxy of GaP nanowire array on Si (111) by MOCVD. , 2019, , .		0
20	Design and growth of multi-functional InAsP metamorphic buffers for mid-infrared quantum well lasers on InP. Journal of Applied Physics, 2019, 125, .	1.1	5
21	High-Quality GaAs Planar Coalescence over Embedded Dielectric Microstructures Using an All-MBE Approach. Crystal Growth and Design, 2019, 19, 3085-3091.	1.4	10
22	Anomalous tilting in InGaAs graded buffers from dislocation sources at wafer edges. Journal of Crystal Growth, 2019, 512, 169-175.	0.7	4
23	Bright Mid-Infrared Photoluminescence from Thin-Film Black Phosphorus. Nano Letters, 2019, 19, 1488-1493.	4.5	90
24	16.8%-Efficient n⁺/p GaAs Solar Cells on Si With High Short-Circuit Current Density. IEEE Journal of Photovoltaics, 2019, 9, 660-665.	1.5	12
25	Delta-doping for enhanced tunnel junction performance and thermal stability. , 2019, , .		1
26	Epitaxial GaAsP/Si Tandem Solar Cells with Integrated Light Trapping. , 2019, , .		2
27	Composition-dependent structural transition in epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Bi</mml:mi><mml:mrow><mml:mn>1</mml:m thin films on Si(111). Physical Review Materials, 2019, 3, .	0.9	6
28	(Al)GaInP/GaAs Tandem Solar Cells for Power Conversion at Elevated Temperature and High Concentration. IEEE Journal of Photovoltaics, 2018, 8, 640-645.	1.5	17
29	Oxide heterostructures for high density 2D electron gases on GaAs. Journal of Applied Physics, 2018, 123, .	1.1	11
30	Solar Cell Analysis Under Venus Atmosphere Conditions. , 2018, , .		1
31	Plasmonically Enhanced Spectral Upconversion for Improved Performance of GaAs Solar Cells under Nonconcentrated Solar Illumination. ACS Photonics, 2018, 5, 4289-4295.	3.2	16
32	Toward deterministic construction of low noise avalanche photodetector materials. Applied Physics Letters, 2018, 113, .	1.5	19
33	Low-Intensity High-Temperature (LIHT) Solar Cells for Venus Atmosphere. IEEE Journal of Photovoltaics, 2018, 8, 1621-1626.	1.5	7
34	10-Fold-Stack Multilayer-Grown Nanomembrane GaAs Solar Cells. ACS Photonics, 2018, 5, 2786-2790.	3.2	7
35	Rare-Earth Monopnictide Alloys for Tunable, Epitaxial, Designer Plasmonics. ACS Photonics, 2018, 5, 3051-3056.	3.2	9
36	Multilayer-Grown Ultrathin Nanostructured GaAs Solar Cells as a Cost-Competitive Materials Platform for IIIâ€“V Photovoltaics. ACS Nano, 2017, 11, 992-999.	7.3	27

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37	Highly tensile-strained Ge/InAlAs nanocomposites. Nature Communications, 2017, 8, 14204.	5.8	15
38	Review Article: Molecular beam epitaxy of lattice-matched InAlAs and InGaAs layers on InP (111)A, (111)B, and (110). Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	41
39	Crystals aligned through graphene. Nature, 2017, 544, 301-302.	13.7	2
40	Solar hydrogen production using epitaxial SrTiO₃ on a GaAs photovoltaic. Energy and Environmental Science, 2017, 10, 377-382.	15.6	46
41	Next-generation mid-infrared sources. Journal of Optics (United Kingdom), 2017, 19, 123001.	1.0	107
42	15.3%-Efficient GaAsP Solar Cells on GaP/Si Templates. ACS Energy Letters, 2017, 2, 1911-1918.	8.8	44
43	Growth rate and surfactant-assisted enhancements of rare-earth arsenide InGaAs nanocomposites for terahertz generation. APL Materials, 2017, 5, 096106.	2.2	5
44	Mid-infrared quantum well lasers on multi-functional metamorphic buffers. , 2017, , .		0
45	Radiation resistant of upright metamorphic GaInP/GaInAs/Ge triple junction solar cells for space use. , 2017, , .		1
46	Computational study of the effect of photovoltaic (PV) module parameters on stress development in silicon under static loading. , 2017, , .		1
47	Notice of Removal Measurements and modeling of III-V solar cells at high temperatures up to 400Â°C. , 2017, , .		1
48	Multilayer-Grown Ultrathin Nanostructured GaAs Solar Cells. , 2017, , .		0
49	Towards High-Efficiency GaAsP/Si Tandem Cells. , 2017, , .		1
50	Electrically pumped continuous-wave 13â€‰â€‰Î¼m quantum-dot lasers epitaxially grown on on-axis (001)â€‰â€‰GaP/Si. Optics Letters, 2017, 42, 338.	1.7	127
51	AlGaInP/GaAs tandem solar cells for power conversion at 400Â°C and high concentration. AIP Conference Proceedings, 2017, , .	0.3	8
52	New Sources and Sensors for Mid- to Far-IR Optical Sensing. , 2017, , .		0
53	Large-scale GaP-on-diamond integrated photonics platform for NV center-based quantum information. Journal of the Optical Society of America B: Optical Physics, 2016, 33, B35.	0.9	29
54	Bulk AlInAs on InP(111) as a novel material system for pure single photon emission. Optics Express, 2016, 24, 23198.	1.7	10

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55	GaAsP solar cells on GaP/Si with low threading dislocation density. Applied Physics Letters, 2016, 109, .	1.5	69
56	Initiation strategies for simultaneous control of antiphase domains and stacking faults in GaAs solar cells on Ge. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	0.6	11
57	Room-temperature mid-infrared quantum well lasers on multi-functional metamorphic buffers. Applied Physics Letters, 2016, 109, .	1.5	15
58	High-efficiency AlGaInP solar cells grown by molecular beam epitaxy. Applied Physics Letters, 2016, 109, .	1.5	19
59	Device and material characteristics of GaInP solar cells grown on Ge substrates by molecular beam epitaxy. , 2016, , .		0
60	GaAsP/Si solar cells and tunnel junctions for III-V/Si tandem devices. , 2016, , .		7
61	Metamorphic epitaxial materials. MRS Bulletin, 2016, 41, 193-198.	1.7	31
62	ICSI-9, MontrÃ©al 2015: Silicon for now and beyond. Thin Solid Films, 2016, 602, 1-2.	0.8	0
63	Threading dislocation density characterization in IIIâ€“V photovoltaic materials by electron channeling contrast imaging. Journal of Crystal Growth, 2016, 453, 65-70.	0.7	23
64	Quaternary Organic Solar Cells Enhanced by Cocrystalline Squaraines with Power Conversion Efficiencies >10%. Advanced Energy Materials, 2016, 6, 1600660.	10.2	46
65	Molecular beam epitaxy growth of germanium junctions for multi-junction solar cell applications. Journal Physics D: Applied Physics, 2016, 49, 465105.	1.3	7
66	Measurements and Modeling of III-V Solar Cells at High Temperatures up to 400 <inline-formula> <tex-math notation="latex">^{circ}</tex-math> </inline-formula>C. IEEE Journal of Photovoltaics, 2016, 6, 1345-1352.	1.5	40
67	Solar Cells: Quaternary Organic Solar Cells Enhanced by Cocrystalline Squaraines with Power Conversion Efficiencies >10% (Adv. Energy Mater. 21/2016). Advanced Energy Materials, 2016, 6, .	10.2	1
68	Large-Area Dry Transfer of Single-Crystalline Epitaxial Bismuth Thin Films. Nano Letters, 2016, 16, 6931-6938.	4.5	87
69	Atomic structure and stoichiometry of In(Ga)As/GaAs quantum dots grown on an exact-oriented GaP/Si(001) substrate. Applied Physics Letters, 2016, 108, .	1.5	8
70	Surfactant-assisted growth and properties of rare-earth arsenide InGaAs nanocomposites for terahertz generation. Applied Physics Letters, 2016, 108, .	1.5	7
71	Direct-Gap 2.1â€“2.2 eV AlInP Solar Cells on GaInAs/GaAs Metamorphic Buffers. IEEE Journal of Photovoltaics, 2016, 6, 571-577.	1.5	10
72	Modeling wide bandgap GaInP photovoltaic cells for conversion efficiencies up to 16.5%. , 2015, , .		2

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73	Mid-infrared electroluminescence from InAs type-I quantum wells grown on InAsP/InP metamorphic buffers. Journal of Applied Physics, 2015, 118, .	1.1	11
74	Single NV Zero-Phonon Line Emission into Waveguide-Coupled GaP-on-Diamond Disk Resonators. , 2015, , .		0
75	Germanium solar cells grown by molecular beam epitaxy for lattice-matched, four-junction solar cells. , 2015, , .		4
76	High performance ultrathin GaAs solar cells. , 2015, , .		7
77	Direct-gap 2.1â€“2.2 eV AlInP solar cells on GaInAs/GaAs metamorphic buffers. , 2015, , .		0
78	Low spatial coherence electrically pumped semiconductor laser for speckle-free full-field imaging. Proceedings of the National Academy of Sciences of the United States of America, 2015, 112, 1304-1309.	3.3	117
79	Synthesis of thin-film black phosphorus on a flexible substrate. 2D Materials, 2015, 2, 031002.	2.0	124
80	Panchromatic polymerâ€“polymer ternary solar cells enhanced by FÃ¶rster resonance energy transfer and solvent vapor annealing. Journal of Materials Chemistry A, 2015, 3, 18611-18621.	5.2	55
81	Growth and properties of rare-earth arsenide InGaAs nanocomposites for terahertz generation. Applied Physics Letters, 2015, 106, .	1.5	20
82	Comparison of single junction AlGaInP and GaInP solar cells grown by molecular beam epitaxy. Journal of Applied Physics, 2015, 117, .	1.1	22
83	Effects of growth temperature and device structure on GaP solar cells grown by molecular beam epitaxy. Applied Physics Letters, 2015, 106, .	1.5	9
84	High Performance Ultrathin GaAs Solar Cells Enabled with Heterogeneously Integrated Dielectric Periodic Nanostructures. ACS Nano, 2015, 9, 10356-10365.	7.3	78
85	Coevaporated Bisquaraine Inverted Solar Cells: Enhancement Due to Energy Transfer and Open Circuit Voltage Control. ACS Photonics, 2015, 2, 86-95.	3.2	47
86	Low Spatial Coherence Electrically Pumped Semiconductor Laser for Speckle-Free Full-Field Imaging. , 2015, , .		1
87	InGaAs/GaAs quantum well lasers grown on exact GaP/Si (001). Electronics Letters, 2014, 50, 1226-1227.	0.5	39
88	Increased InAs quantum dot size and density using bismuth as a surfactant. Applied Physics Letters, 2014, 105, .	1.5	17
89	Waveguide-integrated single-crystalline GaP resonators on diamond. Optics Express, 2014, 22, 13555.	1.7	37
90	Controlling quantum dot energies using submonolayer bandstructure engineering. Applied Physics Letters, 2014, 105, 081103.	1.5	8

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91	Spatially resolved In and As distributions in InGaAs/GaP and InGaAs/GaAs quantum dot systems. Nanotechnology, 2014, 25, 465702.	1.3	2
92	Strain-driven growth of GaAs(111) quantum dots with low fine structure splitting. Applied Physics Letters, 2014, 105, .	1.5	33
93	Metamorphic 2.1-2.2â€‰eV InGaP solar cells on GaP substrates. Applied Physics Letters, 2014, 104, .	1.5	11
94	Effect of substrate effcut angle on AlGaInP and GaInP solar cells grown by molecular beam epitaxy. , 2014, , .		1
95	Towards high efficiency GaAsP solar cells on (001) GaP/Si. , 2014, , .		23
96	Defect selective etching of GaAs P1â^' photovoltaic materials. Journal of Crystal Growth, 2014, 404, 140-145.	0.7	11
97	Tensile GaAs(111) quantum dashes with tunable luminescence below the bulk bandgap. Applied Physics Letters, 2014, 105, .	1.5	12
98	Fabrication of GaP disk resonator arrays coupled to nitrogen-vacancy centers in diamond. Proceedings of SPIE, 2014, , .	0.8	1
99	Waveguiding in polycrystalline GaP grown on SiO2 by molecular beam deposition. , 2014, , .		0
100	InGaAs/GaP quantum dot light-emitting diodes on Si. Applied Physics Letters, 2013, 103, 141906.	1.5	16
101	Single-junction GaAsP solar cells grown on SiGe graded buffers on Si. Applied Physics Letters, 2013, 103, 191901.	1.5	20
102	Polymer bulk heterojunction solar cells employing FÃ¶rster resonance energy transfer. Nature Photonics, 2013, 7, 479-485.	15.6	389
103	Tuning Quantum Dot Luminescence Below the Bulk Band Gap Using Tensile Strain. ACS Nano, 2013, 7, 5017-5023.	7.3	34
104	Improving the performance of P3HT/PCBM solar cells with squaraine dye. Proceedings of SPIE, 2013, , .	0.8	1
105	GaAsP solar cells on GaP/Si grown by molecular beam epitaxy. , 2013, , .		4
106	2.19 eV InGaP solar cells on GaP substrates. , 2013, , .		1
107	Comparison of GaAsP solar cells on GaP and GaP/Si. Applied Physics Letters, 2013, 103, .	1.5	75
108	InAs Quantum Dot Growth Using Bismuth as a Surfactant for Optoelectronic Applications. , 2013, , .		0

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109	GaAsP solar cells on GaP substrates by molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	1.5	19
110	2.8â€‰Î¼m emission from type-I quantum wells grown on InAsxP1â^'x/InP metamorphic graded buffers. Applied Physics Letters, 2012, 101, .	1.5	16
111	Room temperature electroluminescence from light-emitting diodes based on In0.5Ga0.5As/GaP self-assembled quantum dots. Applied Physics Letters, 2012, 100, 251904.	1.5	15
112	Growth of metamorphic GaAsP solar cells on GaP. , 2012, , .		1
113	Metamorphic GaAsP and InGaP Solar Cells on GaAs. IEEE Journal of Photovoltaics, 2012, 2, 56-61.	1.5	21
114	Photoluminescence from In<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub></mml:math>As/GaP quantum dots coupled to photonic crystal cavities. Physical Review B, 2012, 85, .	1.1	25
115	Heterogeneous Integration of InGaAs Nanowires on the Rear Surface of Si Solar Cells for Efficiency Enhancement. ACS Nano, 2012, 6, 11074-11079.	7.3	42
116	Tensile-strained growth on low-index GaAs. Journal of Applied Physics, 2012, 112, .	1.1	26
117	Bioinspired High-Potential Porphyrin Photoanodes. Journal of Physical Chemistry C, 2012, 116, 4892-4902.	1.5	69
118	Heterogeneous Integration of III-V on Si: overcoming the lattice-mismatch barrier via the 1D route. , 2012, , .		0
119	Self-assembly on (111)-oriented III-V surfaces. Applied Physics Letters, 2011, 99, .	1.5	29
120	Molecular beam epitaxy of metamorphic InyGa1â^'yP solar cells on mixed anion GaAsxP1â^'x/GaAs graded buffers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	18
121	Molecular beam epitaxy approach to the graphitization of GaAs(100) surfaces. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C103.	0.6	1
122	Metamorphic GaAsP buffers for growth of wide-bandgap InGaP solar cells. Journal of Applied Physics, 2011, 109, .	1.1	29
123	Graphitized carbon on GaAs(100) substrates. Applied Physics Letters, 2011, 98, 073113.	1.5	3
124	Dislocations and other strain-induced defects in siliconâ€“germanium (SiGe) nanostructures. , 2011, , 338-360.		0
125	Shape transformation of nanoporous GaN by annealing: From buried cavities to nanomembranes. Applied Physics Letters, 2011, 98, .	1.5	40
126	The fabrication of large-area, free-standing GaN by a novel nanoetching process. Nanotechnology, 2011, 22, 045603.	1.3	56

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127	Photoluminescence from In0.5Ga0.5P/GaP quantum dots coupled to photonic crystal cavities. , 2011, , .		0
128	Analysis of SiGe/Si quantum dot superlattices grown by low-pressure chemical vapor deposition for thin solar cells. Thin Solid Films, 2010, 518, S76-S79.	0.8	14
129	Tensile strained III-V self-assembled nanostructures on a (110) surface. Proceedings of SPIE, 2010, , .	0.8	2
130	Growth of Metamorphic InGaP for Wide-Bandgap Photovoltaic Junction by MBE. Materials Research Society Symposia Proceedings, 2010, 1268, 1.	0.1	0
131	Self-assembled In0.5Ga0.5As quantum dots on GaP. Applied Physics Letters, 2010, 97, 223110.	1.5	24
132	Tensile strained island growth at step-edges on GaAs(110). Applied Physics Letters, 2010, 97, .	1.5	17
133	Metamorphic InGaP on GaAs and GaP for wide-bandgap photovoltaic junctions. , 2010, , .		0
134	Si/Ge nanodot superlattices for Si-based photovoltaics. , 2010, , .		0
135	Growth of highly tensile-strained Ge on relaxed InxGa1âˆ'xAs by metal-organic chemical vapor deposition. Journal of Applied Physics, 2008, 104, .	1.1	111
136	Effect of nanodot areal density and period on thermal conductivity in SiGeâˆ•Si nanodot superlattices. Applied Physics Letters, 2008, 92, .	1.5	57
137	High-speed nano-optical photodetector for free space communication. , 2007, , .		1
138	Thermal stability of nonhydrogenated multilayer amorphous carbon prepared by the filtered cathodic vacuum arc technique. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 421-424.	0.9	1
139	Monolithic integration of AlGaInP laser diodes on SiGeâˆ•Si substrates by molecular beam epitaxy. Journal of Applied Physics, 2006, 100, 013103.	1.1	29
140	Ge n-MOSFETs on lightly doped substrates with high-/spl kappa/ dielectric and TaN gate. IEEE Electron Device Letters, 2006, 27, 175-178.	2.2	53
141	Dual junction GaInP/GaAs solar cells grown on metamorphic SiGe/Si substrates with high open circuit voltage. IEEE Electron Device Letters, 2006, 27, 142-144.	2.2	122
142	Fabrication of silicon on lattice-engineered substrate (SOLES) as a platform for monolithic integration of CMOS and optoelectronic devices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 235-237.	1.7	21
143	Challenges in epitaxial growth of SiGe buffers on Si (111), (110), and (112). Thin Solid Films, 2006, 508, 136-139.	0.8	68
144	The electrical properties of HfO/sub 2/ dielectric on germanium and the substrate doping effect. IEEE Transactions on Electron Devices, 2006, 53, 2551-2558.	1.6	20

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145	In situ cleaning effect on the electrical properties of Ge MOS devices by Ar gas anneal. IEEE Transactions on Electron Devices, 2006, 53, 2661-2664.	1.6	5
146	Improved thermal stability and hole mobilities in a strained-Si/strained-Si1â^'yGey/strained-Si heterostructure grown on a relaxed Si1â^'xGex buffer. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 102-106.	1.7	1
147	Investigations of High-Performance GaAs Solar Cells Grown on Geâ€"Si<tex>$_1-xhbox Ge_ x$</tex>â€"Si Substrates. IEEE Transactions on Electron Devices, 2005, 52, 1055-1060.	1.6	70
148	Positive Temperature Coefficient of Impact Ionization in Strained-Si. IEEE Transactions on Electron Devices, 2005, 52, 1627-1633.	1.6	11
149	Improved hole mobilities and thermal stability in a strainedâ€Siâ^•strainedâ€Si1â^'yGeyâ^•strainedâ€Si heterostructure grown on a relaxed Si1â^'xGex buffer. Applied Physics Letters, 2005, 86, 192104.	1.5	10
150	Dislocation engineering in strained mos materials. , 2005, , .		1
151	Effect of Pt on agglomeration and Ge out diffusion in Ni(Pt) germanosilicide. Journal of Applied Physics, 2005, 98, 033520.	1.1	28
152	Growth and properties of AlGaInP resonant cavity light emitting diodes on Geâ^•SiGeâ^•Si substrates. Journal of Applied Physics, 2005, 97, 034504.	1.1	10
153	Highly oriented Ni(Pd)SiGe formation at 400â€‰Â°C. Journal of Applied Physics, 2005, 97, 104917.	1.1	14
154	Comparison of low-temperature GaN, SiO2, and SiNx as gate insulators on AlGaNâ^•GaN heterostructure field-effect transistors. Journal of Applied Physics, 2005, 98, 064506.	1.1	20
155	Impact of dislocation densities on n+â^•p and p+â^•n junction GaAs diodes and solar cells on SiGe virtual substrates. Journal of Applied Physics, 2005, 98, 014502.	1.1	112
156	Ge diffusion in Ge metal oxide semiconductor with chemical vapor deposition HfO2 dielectric. Applied Physics Letters, 2005, 87, 051922.	1.5	119
157	Strained Si, SiGe, and Ge channels for high-mobility metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2005, 97, 011101.	1.1	818
158	Hole mobility enhancement in strained-Si/strained-SiGe heterostructure p-MOSFETs fabricated on SiGe-on-insulator (SGOI). Semiconductor Science and Technology, 2004, 19, L48-L51.	1.0	13
159	Growth of strained Si and strained Ge heterostructures on relaxed Si[sub 1â^'x]Ge[sub x] by ultrahigh vacuum chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 158.	1.6	47
160	Ultracompact, multifunctional, and highly integrated 3Ã—2 photonic switches. Applied Physics Letters, 2004, 84, 2241-2243.	1.5	17
161	Fully Depleted Strained-SOI n- and p-MOSFETs on Bonded SGOI Substrates and Study of the SiGe/BOX Interface. IEEE Electron Device Letters, 2004, 25, 147-149.	2.2	13
162	Effect of thermal processing on mobility in strained Si/strained Si1â^'yGey on relaxed Si1â^'xGexâ€Š(x<y) virtual substrates. Applied Physics Letters, 2004, 84, 3319-3321.	1.5	25

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163	Coplanar Integration of Lattice-Mismatched Semiconductors with Silicon by Wafer Bonding Ge/Si[sub 1â^'x]Ge[sub x]/Si Virtual Substrates. Journal of the Electrochemical Society, 2004, 151, G443.	1.3	31
164	Mobility Enhancement in Dual-Channel P-MOSFETs. IEEE Transactions on Electron Devices, 2004, 51, 1424-1431.	1.6	11
165	Impact of Ion Implantation Damage and Thermal Budget on Mobility Enhancement in Strained-Si N-Channel MOSFETs. IEEE Transactions on Electron Devices, 2004, 51, 2136-2144.	1.6	19
166	The interfacial reaction of Ni with (111)Ge, (100)Si0.75Ge0.25 and (100)Si at 400 Â°C. Thin Solid Films, 2004, 462-463, 151-155.	0.8	31
167	On the mechanism of ion-implanted As diffusion in relaxed SiGe. Applied Surface Science, 2004, 224, 59-62.	3.1	9
168	Electron mobility characteristics of n-channel metal-oxide-semiconductor field-effect transistors fabricated on Ge-rich single- and dual-channel SiGe heterostructures. Journal of Applied Physics, 2004, 95, 1550-1555.	1.1	11
169	Impact of dislocations on minority carrier electron and hole lifetimes in GaAs grown on metamorphic SiGe substrates. Applied Physics Letters, 2004, 84, 3447-3449.	1.5	93
170	Ultrathin Strained Si-on-Insulator and SiGe-on-Insulator Created using Low Temperature Wafer Bonding and Metastable Stop Layers. Journal of the Electrochemical Society, 2004, 151, G47.	1.3	29
171	Fabrication of ultra-thin strained silicon on insulator. Journal of Electronic Materials, 2003, 32, 972-975.	1.0	29
172	Implementation of both high-hole and electron mobility in strained Si/strained Si_{1-y}Ge_y on relaxed Si_{1-x}Ge_x (x<y) virtual substrate. IEEE Electron Device Letters, 2003, 24, 460-462.	2.2	57
173	Growth and Properties of AlGaInP Resonant Cavity Light Emitting Diodes (RCLEDs)on Ge/SiGe/Si Substrates. Materials Research Society Symposia Proceedings, 2003, 799, 111.	0.1	0
174	Effect of rapid thermal annealing on strain in ultrathin strained silicon on insulator layers. Applied Physics Letters, 2003, 83, 875-877.	1.5	41
175	Hole mobility enhancements in nanometer-scale strained-silicon heterostructures grown on Ge-rich relaxed Si1â^'xGex. Journal of Applied Physics, 2003, 94, 2590-2596.	1.1	51
176	Strained Si/strained Ge dual-channel heterostructures on relaxed Si0.5Ge0.5 for symmetric mobility p-type and n-type metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2003, 83, 4202-4204.	1.5	63
177	Hybrid Valence Bands in Strained-Layer Heterostructures grown on Relaxed SiGe Virtual Substrates. Materials Research Society Symposia Proceedings, 2003, 768, 1101.	0.1	1
178	Hybrid Valence Bands in Strained-Layer Heterostructures grown on Relaxed SiGe Virtual Substrates. Materials Research Society Symposia Proceedings, 2003, 765, 1.	0.1	0
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